

L Number	Hits	Search Text	DB	Time stamp
3	6329	(250/306,307,310,311,492.3,492.2,492.22).C	USPAT; US-PGPUB	2004/11/03 15:45
4	6329	((250/306,307,310,311,492.3,492.2,492.22))	USPAT; US-PGPUB	2004/11/03 15:46
5	14947	((250/306,307,310,311,492.3,492.2,492.22) and (silicon adj on adj insulator) or SOI	USPAT; US-PGPUB	2004/11/03 15:47
6	75	((250/306,307,310,311,492.3,492.2,492.22) and ((silicon adj on adj insulator) or	USPAT; US-PGPUB	2004/11/03 15:47
7	7	\$(250/306,307,310,311,492.3,492.2,492.22) and ((silicon adj on adj insulator) or	USPAT; US-PGPUB	2004/11/03 15:51
8	2	((250/306,307,310,311,492.3,492.2,492.22) and ((silicon adj on adj insulator) or	USPAT; US-PGPUB	2004/11/03 15:48
9	23068	((250/306,307,310,311,492.3,492.2,492.22) and ((silicon adj on adj insulator) or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/03 15:49
10	0	((silicon adj on adj insulator) or SOI) and (semiconductor near2 die)and (inspection with (electron or SEM))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/03 15:50
11	0	((silicon adj on adj insulator) or SOI) and (semiconductor near2 die) and (inspect\$5 with (electron or SEM))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/03 15:51
12	8	((silicon adj on adj insulator) or SOI) and (semiconductor near2 (wafer or die)) and (inspect\$5 with (electron or SEM))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/03 15:50
13	8	((silicon adj on adj insulator) or SOI) and (semiconductor near2 (wafer or die)) and (inspect\$5 with (electron or SEM)) ) and (semiconductor near2 (wafer or die)) and (inspect\$5 with (electron or SEM))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/03 15:51
14	4	((silicon adj on adj insulator) or SOI) and (semiconductor near2 (wafer or die)) and (inspect\$5 with (electron or SEM)) ) and (semiconductor near2 (wafer or die)) and (inspect\$5 with (electron or SEM)) ) and ((electron adj beam) or SEM) and (substrate near2 remov\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/03 15:52